Notice of Allowability	Application No.	Applicant(s)
	10/667,601	CHIDAMBARRAO ET AL.
	Examiner	Art Unit
	Kyoung Lee	2812
The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308. 1. This communication is responsive to 09/23/2003.		
2. The allowed claim(s) is/are <u>1-16,21,22 and 24-26</u> .		ALEXANDER GHYKA
Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a)		
Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 12/13/05, 10/11/05 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. ☐ Interview Summary Paper No./Mail Dat 8), 7. ☐ Examiner's Amenda	e

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DETAILED ACTION

REASONS FOR ALLOWANCE

Claims 1-16, 21-22, and 24-26 are allowed.

The following is an examiner's statement of reasons for allowance: claim 1 is allowed because of the prior art, either singly or in combination, fails to anticipate or render obvious, the method, including steps of forming an oxide formed during the oxidizing step from above the gate polysilicon of the n-type transistor, wherein the oxidizing step results in formation of a bird's beak in an edge of the gate polysilicon between the gate polysilicon and a spacer of the n-type transistor and the removing step preserves the bird's beak. These features in combination with the other elements of the claim are neither disclosed nor suggested by the prior art of record.

Claims 2-9, 13-15, 21-22, and 26 depend from claim 1, so they are allowed for the same reason.

The following is an examiner's statement of reasons for allowance: claim 10 is allowed because of the prior art, either singly or in combination, fails to anticipate or render obvious, the method including steps of depositing silicide material on at least the portion of the gate polysilicon of the n-type field effect transistor. These features in combination with the other elements of the claim are neither disclosed nor suggested by the prior art of record.

Claims 11 and 12 depend from claim 10, so they are allowed for the same reason.

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The following is an examiner's statement of reasons for allowance: claim 24 is allowed because of the prior art, either singly or in combination, fails to anticipate or render obvious, the method, including steps of forming a first oxide above a gate polysilicon and between a side of the gate polysilicon and a spacer of the n-type transistor and removing the first oxide from above the gate polysilicon of the n-type transistor while allowing the first oxide to remain between the side of the gate polysilicon and the spacer. These features in combination with the other elements of the claim are neither disclosed nor suggested by the prior art of record.

Claim 25 depends from claim 24, so they are allowed for the same reason.

CONCLUSION

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Kyoung Lee whose telephone number is (571) 272-1982. The examiner can normally be reached on M-F 8:30AM - 5:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael S. Lebentritt can be reached on (571) 272-1873. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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